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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit
Speed	50.33MHz
Connectivity	CANbus, I ² C, SCI, SPI, UART/USART
Peripherals	LVD, PWM, WDT
Number of I/O	69
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 24x12b SAR
Oscillator Type	External, Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51ac256avlke



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1.3.1 Feature List

- 32-bit Version 1 ColdFire® central processor unit (CPU)
 - Up to 50.33 MHz at 2.7 V 5.5 V
 - Provide 0.94 Dhrystone 2.1 DMIPS per MHz performance when running from internal RAM (0.76 DMIPS per MHz when running from flash)
 - Implements instruction set revision C (ISA_C)
- On-chip memory
 - Up to 256 KB flash memory read/program/erase over full operating voltage and temperature
 - Up to 32 KB static random access memory (SRAM)
 - Security circuitry to prevent unauthorized access to SRAM and flash contents
- Power-Saving Modes
 - Three low-power stop plus wait modes
 - Peripheral clock enable register can disable clocks to unused modules, reducing currents; allows clocks to remain enabled to specific peripherals in stop3 mode
- System protection features
 - Watchdog computer operating properly (COP) reset with options to run from independent LPO clock or bus clock
 - Low-voltage detection with reset or interrupt
 - Illegal opcode and illegal address detection with programmable reset or exception response
 - Flash block protection
- · Debug support
 - Single-wire background debug interface
 - Real-time debug support, with 6 hardware breakpoints (4 PC, 1 address pair and 1 data) that can be configured into a 1- or 2-level trigger
 - On-chip trace buffer provides programmable start/stop recording conditions plus support for continuous or PC-profiling modes
 - Support for real-time program (and optional partial data) trace using the debug visibility bus
- V1 ColdFire interrupt controller (CF1 INTC)
 - Support of 40 peripheral I/O interrupt requests plus seven software (one per level) interrupt requests
 - Fixed association between interrupt request source and level plus priority, up to two requests can be remapped to the highest maskable level + priority
 - Unique vector number for each interrupt source
 - Support for service routine interrupt acknowledge (software IACK) read cycles for improved system performance
- Multipurpose clock generator (MCG)
 - Oscillator (XOSC); loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
 - LPO clock as an optional independent clock source for COP and RTI
 - FLL/PLL controlled by internal or external reference



- Inter-integrated circuit (IIC)
 - Compatible with IIC bus standard
 - Multi-master operation
 - Software programmable for one of 64 different serial clock frequencies
 - Interrupt driven byte-by-byte data transfer
 - Arbitration lost interrupt with automatic mode switching from master to slave
 - Calling address identification interrupt
 - Bus busy detection
 - 10-bit address extension
- Controller area network (CAN)
 - Implementation of the CAN protocol Version 2.0A/B
 - Standard and extended data frames
 - Zero to eight bytes data length
 - Programmable bit rate up to 1 Mbps
 - Support for remote frames
 - Five receive buffers with FIFO storage scheme
 - Three transmit buffers with internal prioritization using a "local priority" concept
 - Flexible maskable identifier filter supports two full-size (32-bit) extended identifier filters, four 16-bit filters, or eight 8-bit filters
 - Programmable wakeup functionality with integrated low-pass filter
 - Programmable loopback mode supports self-test operation
 - Programmable listen-only mode for monitoring of CAN bus
 - Programmable bus-off recovery functionality
 - Separate signalling and interrupt capabilities for all CAN receiver and transmitter error states (warning, error passive, bus-off)
 - Internal timer for time-stamping of received and transmitted messages
- Serial communications interfaces (SCI)
 - Full-duplex, standard non-return-to-zero (NRZ) format
 - Double-buffered transmitter and receiver with separate enables
 - Programmable baud rates (13-bit modulo divider)
 - Interrupt-driven or polled operation
 - Hardware parity generation and checking
 - Programmable 8-bit or 9-bit character length
 - Receiver wakeup by idle-line or address-mark
 - Optional 13-bit break character generation / 11-bit break character detection
 - Selectable transmitter output polarity
- Serial peripheral interfaces (SPI)
 - Master or slave mode operation
 - Full-duplex or single-wire bidirectional option
 - Programmable transmit bit rate

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



MCF51AC256 Family Configurations

- Double-buffered transmit and receive
- Serial clock phase and polarity options
- Slave select output
- Selectable MSB-first or LSB-first shifting
- 16-bit and FIFO operations in SPI2
- Input/Output
 - 69 GPIOs
 - 8 keyboard interrupt pins with selectable polarity
 - Hysteresis and configurable pull-up device on all input pins; Configurable slew rate and drive strength on all output pins
 - 16-bits Rapid GPIO pins connected to the processor's local 32-bit platform bus with set, clear, and faster toggle functionality

1.4 Part Numbers

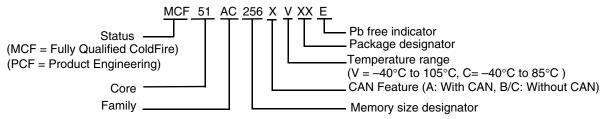


Table 3. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (Kbytes)	Package	Temperature
MCF51AC256AVFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256BVFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	–40°C to 105°C
MCF51AC256AVLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 105°C
MCF51AC256BVLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	-40°C to 105°C
MCF51AC256AVPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	-40°C to 105°C
MCF51AC256BVPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	-40°C to 105°C
MCF51AC128AVFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	-40°C to 105°C
MCF51AC128CVFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	-40°C to 105°C
MCF51AC128AVLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 105°C
MCF51AC128CVLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	-40°C to 105°C
MCF51AC128AVPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	-40°C to 105°C
MCF51AC128CVPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	-40°C to 105°C
MCF51AC256ACFUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 QFP	–40°C to 85°C
MCF51AC256BCFUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 QFP	-40°C to 85°C
MCF51AC256ACLKE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	80 LQFP	–40°C to 85°C
MCF51AC256BCLKE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	80 LQFP	-40°C to 85°C

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



MCF51AC256 Family Configurations

Table 3. Orderable Part Number Summary

MCF51AC256ACPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCFGE	MCF51AC256 ColdFire Microcontroller without CAN	256/32	44 LQFP	–40°C to 85°C
MCF51AC128ACFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 85°C
MCF51AC128CCFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 85°C
MCF51AC128ACLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 85°C
MCF51AC128CCLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 85°CC
MCF51AC128ACPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 85°C
MCF51AC128CCPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 85°C
MCF51AC128CCFGE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	44 LQFP	–40°C to 85°C



Table 4. Pin Availability by Package Pin-Count (continued)

Pin Number		Lowe	est < Pric	ority> Hi	ghest	
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
8	8	6	PTF4	RGPIO12	FTM2CH0	
9	9	_	PTC6	FTM2FLT		
10	10	_	PTF7	RGPIO15		
11	11	7	PTF5	RGPIO13	FTM2CH1	
12	12	_	PTF6	RGPIO14	FTM1FLT	
13		_	PTJ0	PST0		
14		_	PTJ1	PST1		
15		_	PTJ2	PST2		
16		_	PTJ3	PST3		
17	13	8	PTE0	RGPIO0	TxD1	
18	14	9	PTE1	RGPIO1	RxD1	
19	15	10	PTE2	RGPIO2	FTM1CH0	
20	16	11	PTE3	RGPIO3	FTM1CH1	
21	17	12	PTE4	RGPIO4	SS1	
22	18	13	PTE5	RGPIO5	MISO1	
23	19	14	PTE6	RGPIO6	MOSI1	
24	20	15	PTE7	RGPI07	SPSCK1	
25	21	16	V_{SS}			
26	22	17	V_{DD}			
27	_	_	PTJ4	DDATA0		
28	_	_	PTJ5	DDATA1		
29	_	_	PTJ6	DDATA2		
30	_	_	PTJ7	DDATA3		
31	23	18	PTG0	KBI1P0		
32	24	19	PTG1	KBI1P1		
33	25	20	PTG2	KBI1P2		
34	26	21	PTA0	TxCAN ²		
35	27	22	PTA1	RxCAN ³		
36	28	_	PTA2			
37	29	_	PTA3	ACMP2O		
38	30	_	PTA4	ACMP2-		
39	31	_	PTA5	ACMP2+		
40	32	_	PTA6	AD1P16		
41	33	_	PTA7	AD1P17		
42	_	_	PTH0	FTM2CH2	AD1P20	
43	_	_	PTH1	FTM2CH3	PSTCLK0	AD1P21
44	_	_	PTH2	FTM2CH4	PSTCLK1	AD1P22
45	_	_	PTH3	FTM2CH5	BKPT	AD1P23
46	34	23	PTB0	TPM3CH0	AD1P0	
47	35	24	PTB1	TPM3CH1	AD1P1	
48	36	25	PTB2	AD1P2		

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



- Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance
- ² Junction to Ambient Natural Convection
- ³ 1s Single layer board, one signal layer
- ⁴ 2s2p Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_I) in ${}^{\circ}C$ can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 $T_A = Ambient temperature, °C$

 θ_{IA} = Package thermal resistance, junction-to-ambient, °C/W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power

 $P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_A + 273^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273^{\circ}C) + \theta_{JA} \times (P_D)^2$$
 Eqn. 3

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A .

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete dc parametric and functional testing is performed per the



applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 8. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human body	Series resistance	R1	1500	Ω
	Storage capacitance	С	100	pF
	Number of pulse per pin	_	3	
Charge device	Series resistance	R1	0	Ω
model	Storage capacitance	С	0	pF
	Number of pulse per pin	_	3	_
Latch-up	Minimum input voltage limit	_	-2.5	V
	Maximum input voltage limit	_	7.5	٧

Table 9. ESD and Latch-Up Protection Characteristics

Num	Rating	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	±2000		V
2	Charge device model (CDM)	V _{CDM}	±500	_	V
3	Latch-up current at T _A = 85 °C	I _{LAT}	±100		mA

2.5 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Table 10. DC Characteristics

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	—	Operating voltage		2.7	_	5.5	V
		Output high voltage — Low drive (PTxDSn = 0)					
		5 V, $I_{Load} = -4 \text{ mA}$		V _{DD} – 1.5	_	_	
		3 V, $I_{Load} = -2 \text{ mA}$		V _{DD} – 1.5	_	_	
		5 V, $I_{Load} = -2 \text{ mA}$		$V_{DD} - 0.8$		_	
2	Р	3 V, $I_{Load} = -1 \text{ mA}$	V	$V_{DD} - 0.8$	_	_	V
	'	Output high voltage — High drive (PTxDSn = 1)	V _{OH}				V
		5 V, $I_{Load} = -15 \text{ mA}$		V _{DD} – 1.5	_	_	
		3 V, $I_{Load} = -8 \text{ mA}$		V _{DD} – 1.5		_	
		5 V, $I_{Load} = -8 \text{ mA}$		$V_{DD} - 0.8$	_	_	
		3 V, $I_{Load} = -4 \text{ mA}$		$V_{DD}^{-1} - 0.8$	_	_	



Table 10. DC Characteristics (continued)

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
		DC injection current $^{5\ 6\ 7\ 8}$ (single pin limit) $V_{IN}>V_{DD}$ V_{IN}		0 0	_	2 -0.2	mA
22		DC injection current (Total MCU limit, includes sum of all stressed pins) $ \frac{V_{IN}>V_{DD}}{V_{IN}< V_{SS}} $	I _{IC}	0 0		25 -5	mA

Typical values are based on characterization data at 25°C unless otherwise stated.

- $^{6}\,$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} .
- Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
- 8 The $\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD} . Do not drive this pin above V_{DD} .

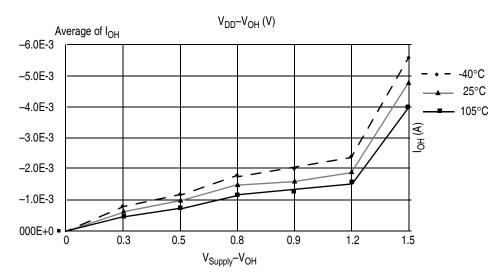


Figure 5. Typical I_{OH} vs. V_{DD}-V_{OH} at V_{DD} = 3 V (Low Drive, PTxDSn = 0)

² Measured with $V_{In} = V_{DD}$ or V_{SS} .

 $^{^{3}}$ Measured with $V_{In} = V_{SS}$.

⁴ Measured with $V_{In} = V_{DD}$.

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).



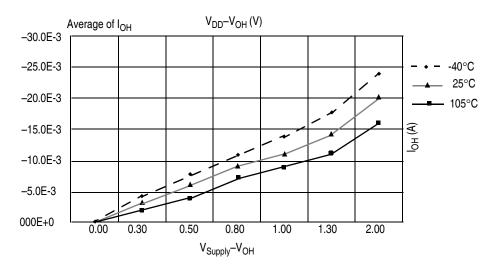


Figure 8. Typical I_{OH} vs. V_{DD} – V_{OH} at V_{DD} = 5 V (High Drive, PTxDSn = 1)



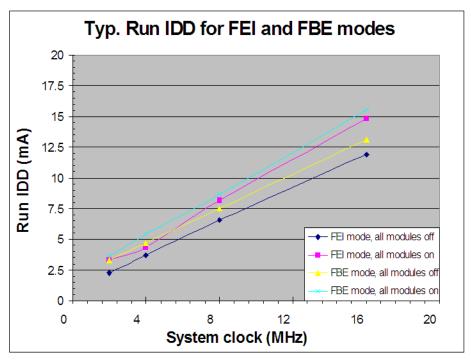


Figure 9. Typical Run $\rm I_{DD}$ vs. System Clock Freq. for FEI and FBE Modes

2.7 Analog Comparator (ACMP) Electricals

Table 12. Analog Comparator Electrical Specifications

Num	С	Rating	Symbol	Min	Typical	Max	Unit
1	_	Supply voltage	V_{DD}	2.7	_	5.5	V
2	Т	Supply current (active)	I _{DDAC}	_	20	35	μА
3	D	Analog input voltage	V _{AIN}	$V_{SS} - 0.3$	_	V_{DD}	V
4	D	Analog input offset voltage	V _{AIO}	_	20	40	mV
5	D	Analog comparator hysteresis	V _H	3.0	6.0	20.0	mV
6	D	Analog input leakage current	I _{ALKG}	_	_	1.0	μА
7	D	Analog comparator initialization delay	t _{AINIT}	_	_	1.0	μS
8	Р	Bandgap voltage reference factory trimmed at $V_{DD} = 5.3248 \text{ V}$, Temp = 25 °C	V_{BG}	1.18	1.20	1.21	V



2.8 ADC Characteristics

Table 13. 5 Volt 12-bit ADC Operating Conditions

Num	С	Characteristic	Conditions	Symb	Min	Typical ¹	Max	Unit	Comment
	D		Absolute	V_{DDA}	2.7	_	5.5	٧	
1	D	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA}) ²	ΔV_{DDA}	-100	0	100	mV	
2	D	Ground voltage	Delta to V _{SS} $(V_{SS} - V_{SSA})^2$	ΔV _{SSA}	-100	0	100	mV	
3	D	Reference voltage high		V _{REFH}	2.7	V_{DDA}	V _{DDA}	٧	
4	D	Reference voltage low		V _{REFL}	V _{SSA}	V _{SSA}	V _{SSA}	٧	
5	D	Input voltage		V _{ADIN}	V _{REFL}	_	V _{REFH}	V	
6	С	Input capacitance		C _{ADIN}	_	4.5	5.5	pF	
7	С	Input resistance		R _{ADIN}	_	3	5	kΩ	
	С		12-bit mode f _{ADCK} > 4MHz f _{ADCK} < 4MHz				2 5		
8	С	Analog source resistance	10-bit mode f _{ADCK} > 4MHz f _{ADCK} < 4MHz	R _{AS}	_		5 10	kΩ	External to MCU
	С		8-bit mode (all valid f _{ADCK})		_	_	10		
9	D	ADC conversion	High speed (ADLPC = 0)	f	0.4	_	8.0	MHz	
9	D	clock frequency	Low power (ADLPC = 1)	f _{ADCK}	0.4	_	4.0	IVI∏∠	

Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

² DC potential difference.



Table 14. 5 Volt 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

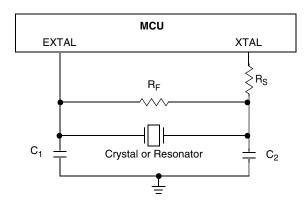
ſ						1					
Num	С	Characteristic	Conditions	Symb	Min	Typical ¹	Max	Unit	Comment		
7	P	Conversion time (including sample time)	Short sample (ADLSMP = 0)	t _{ADC}	tano	_	20	_	ADCK	See	
,	, '		Long sample (ADLSMP = 1)		_	40	_	cycles	Table 10 for		
8	Т	Sample time	Short sample (ADLSMP = 0)	t _{ADS}	_	3.5	_	ADCK cycles	conversion time variances		
		Campio timo	Long sample (ADLSMP = 1)		_	23.5	_				
	Т	Total unadjusted error	12-bit mode	E _{TUE}	_	±3.0	_		Includes		
9	Р		10-bit mode		E _{TUE}	E _{TUE} -	_	±1 ±2.5	±2.5	LSB ²	quantizatio
	Т		8-bit mode		_	±0.5	±1.0	İ	n		
	Т		12-bit mode		_	±1.75	_	LSB ²			
10	Р	Differential non-linearity	10-bit mode ³	DNL	_	±0.5	±1.0				
	Т		8-bit mode ³		_	±0.3	±0.5				
	Т		12-bit mode	INL	_	±1.5	_	LSB ²			
11	Т	Integral non-linearity	10-bit mode		_	±0.5	±1.0				
	Т		8-bit mode		_	±0.3	±0.5				
	Т	Zero-scale error	12-bit mode	E _{ZS}	_	±1.5	_	LSB ²	V _{ADIN} = V _{SSA}		
12	2 P		10-bit mode		_	±0.5	±1.5				
			8-bit mode		_	±0.5	±0.5				
	Т		12-bit mode		_	±1	_	LSB ²	V _{ADIN} = V _{DDA}		
13	Р	Full-scale error	10-bit mode	E _{FS}	_	±0.5	±1				
	Т		8-bit mode		_	±0.5	±0.5				
			12-bit mode		_	-1 to 0	_				
14	D	Quantization error	10-bit mode	EQ	_	_	±0.5	LSB ²			
			8-bit mode		_	_	±0.5				
			12-bit mode		_	±1	_		Pad		
15	D	Input leakage error	10-bit mode	E _{IL}	_	±0.2	±2.5	LSB ²	leakage ⁴ *		
			8-bit mode		_	±0.1	±1		R _{AS}		
16	D	Temp sensor voltage	25°C	V _{TEMP25}	_	1.396	_	V			
17	_	D Temp sensor slope	–40 °C–25 °C	- m		_	3.266	_	m\//00		
17	ט		25 °C–85 °C		_	3.638 — mV/°C					

Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

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² 1 LSB = $(V_{REFH} - V_{REFL})/2^N$.





2.10 MCG Specifications

Table 16. MCG Frequency Specifications (Temperature Range = -40 to 105 °C Ambient)

Num	С	Rating		Symbol	Min	Typical ¹	Max	Unit
1	С	Internal reference frequency — factory trimmed at $V_{DD} = 5 \text{ V}$ and temperature = 25 °C		f _{int_ft}	_	32.768	_	kHz
2	С	Average internal reference	frequency — untrimmed	f _{int_ut}	31.25	_	39.0625	kHz
3	Т	Internal reference startup ti	ime	t _{irefst}	_	60	100	μS
	С	DCO output frequency range — untrimmed ²	Low range (DRS=00)		16		20	MHz
4	С		Mid range (DRS=01)	f _{dco_ut}	32	_	40	
	С	Tango unummou	High range (DRS=10)		48	_	60	
	Р	DCO output frequency ² reference =32768Hz and DMX32 = 1	Low range (DRS=00)	f _{dco_DMX32}	_	16.82	_	MHz
5	Р		Mid range (DRS=01)			33.69		
	Р		High range (DRS=10)			50.48		
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco_res_t}$	_	±0.1	±0.2	%f _{dco}
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco_res_t}$	_	±0.2	±0.4	%f _{dco}
8	D	Total deviation of trimmed DCO output frequency over voltage and temperature		Δf_{dco_t}	_	0.5 -1.0	±2	%f _{dco}
9	D	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0–70 °C		Δf_{dco_t}	_	±0.5	±1	%f _{dco}
10	D	FLL acquisition time ³		t _{fll_acquire}		_	1	ms
11	D	PLL acquisition time ⁴		t _{pll_acquire}		_	1	ms
12	D	Long term jitter of DCO output clock (averaged over 2ms interval) ⁵		C _{Jitter}	_	0.02	0.2	%f _{dco}
13	D	VCO operating frequency		f _{vco}	7.0	_	55.0	MHz
16	D	Jitter of PLL output clock measured over 625 ns ⁶		f _{pll_jitter_625ns}	_	0.566 ⁶	_	%f _{pll}
17	D	Lock entry frequency tolera	D _{lock}	±1.49		±2.98	%	



Control Timing 2.11.1

Table 17. Control Timing

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
1	D	Bus frequency (t _{cyc} = 1/f _{Bus})	f _{Bus}	dc	_	24	MHz
2	D	Internal low-power oscillator period	t _{LPO}	800	_	1500	μS
3	D	External reset pulse width ² $(t_{cyc} = 1/f_{Self_reset})$	t _{extrst}	100	_	_	ns
4	D	Reset low drive	t _{rstdrv}	$66 \times t_{cyc}$	_		ns
5	D	Active background debug mode latch setup time	t _{MSSU}	500	_	_	ns
6	D	Active background debug mode latch hold time	t _{MSH}	100	-	_	ns
7	D	IRQ pulse width Asynchronous path ² Synchronous path ³	t _{ILIH,} t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
8	D	KBIPx pulse width Asynchronous path ² Synchronous path ³	t _{ILIH,} t _{IHIL}	100 1.5 × t _{cyc}	_	_	ns
9	D	Port rise and fall time (load = 50 pF) ⁴ Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive Slew rate control disabled (PTxSE = 0), Low Drive Slew rate control enabled (PTxSE = 1), Low Drive	t _{Rise} , t _{Fall}	_ _ _ _	11 35 40 75	_	ns

Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

 $^{^4}$ Timing is shown with respect to 20% $\rm V_{DD}$ and 80% $\rm V_{DD}$ levels. Temperature range –40 $^{\circ}C$ to 105 $^{\circ}C$.

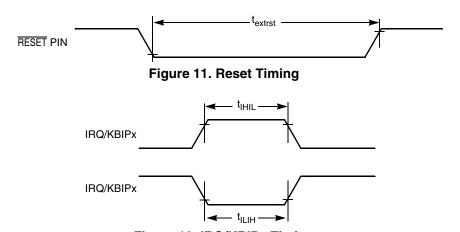


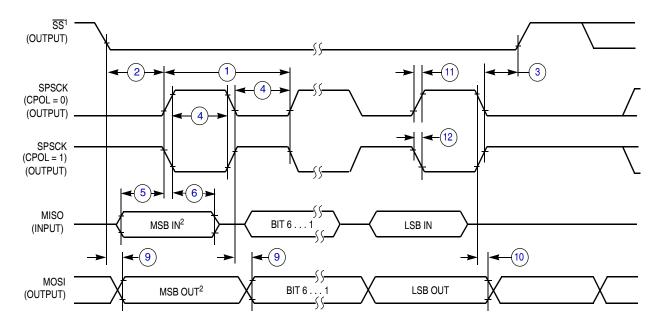
Figure 12. IRQ/KBIPx Timing

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² This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

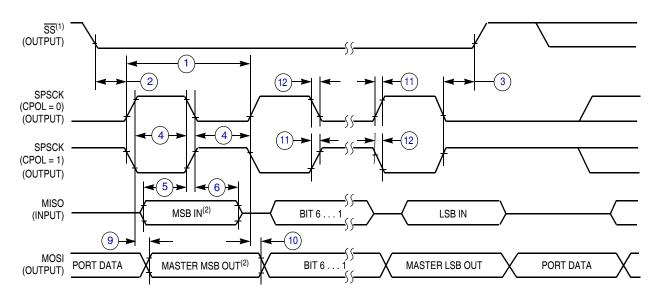




NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI Master Timing (CPHA = 0)



NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 16. SPI Master Timing (CPHA =1)



Num	С	Characteristic	Symbol	Min	Typical ¹	Max	Unit
1	_	Supply voltage for program/erase	V _{prog/erase}	2.7	_	5.5	V
2	_	Supply voltage for read operation	V _{Read}	2.7	_	5.5	V
3		Internal FCLK frequency ²	f _{FCLK}	150	_	200	kHz
4		Internal FCLK period (1/FCLK)	t _{Fcyc}	5	_	6.67	μS
5		Byte program time (random location) ²	t _{prog}	9			t _{Fcyc}
6		Byte program time (burst mode) ² t _{Burst} 4			t _{Fcyc}		
7		Page erase time ³	t _{Page}	4000		t _{Fcyc}	
8		Mass erase time ²	t _{Mass}	20,000		t _{Fcyc}	
9	О	Program/erase endurance ⁴ T_L to $T_H = -40$ °C to 105 °C $T = 25$ °C	_	10,000 —	 100,000		cycles
10	С	Data retention ⁵	t _{D_ret}	15	100	_	years

Table 21. Flash Characteristics

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

² The frequency of this clock is controlled by a software setting.

These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

Typical endurance for flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, Typical Endurance for Nonvolatile Memory.

Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.



Mechanical Outline Drawings

3 Mechanical Outline Drawings

Table 22 provides the available package types and their document numbers. The latest package outline/mechanical drawings are available on the MCF51AC256 Series Product Summary pages at http://www.freescale.com.

To view the latest drawing, either:

- Click on the appropriate link in Table 22, or
- Open a browser to the Freescale E website (http://www.freescale.com), and enter the appropriate document number (from Table 22) in the "Enter Keyword" search box at the top of the page.

Table 22. Package Information

Pin Count	Туре	Document No.
80	LQFP	98ARL10530D
64	LQFP	98ASS23234W
64	QFP	98ASB42844B
44	LQFP	98ASS23225W



4 Revision History

Table 23. Revision History

Revision	Description
1	Initial published
2	Updated ADC channels, Item 1, 4-5 on Table 2.10
3	Completed all the TBDs. Changed RTC to RTI in Figure 1. Corrected the block diagram. Changed V_{DDAD} to V_{DDA} , V_{SSAD} to V_{SSA} . Added charge device model data and removed machine data in Table 8. Updated the specifications of V_{LVDH} , V_{LVDL} , V_{LVWH} and V_{LVWL} in Table 10. Updated $S2I_{DD}$, $S3I_{DD}$ in Table 11. Added C column in Table 14. Updated f_{dco_DMX32} in Table 16.
4	Corrected the expansion of SPI to serial peripheral interface.
5	Updated V _{LVDL} in the Table 10. Updated RI _{DD} in the Table 11.
6	Updated V _{LVDH} , V _{LVDL} , V _{LVWH} and V _{LVWL} in the Table 10. Added LPO on the Figure 1 and LPO features in the Section 1.3, "Features."
7	Added 44-pin LQFP package information for AC256 and AC128.



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